

ABSTRACT

A first thermal treatment, which is performed at a temperature within 650-750°C for 30- 240 minutes, and thereafter a second thermal treatment, which is performed at a temperature within 900-1100°C for 30-120 minutes, are performed as the initial thermal treatments on a semiconductor wafer composed of silicon. Further, before forming a gate insulating film, the temperature is increased to 1000°C at a temperature increasing rate of 8°C/min in a nitrogen ambient, and a thermal treatment is performed at a temperature of 1000°C for 30 minutes as a third thermal treatment.